

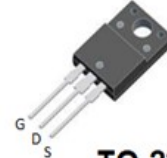
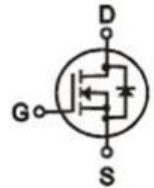
**Product Summary**

BVDSS	RDSON	ID
800V	1.0Ω	10A

**Application**

- Switch Mode Power Supply(SMPS)
- Uninterruptible Power Supply(UPS)
- Power Factor Correction (PFC)

- Improved dv/dt Capability
- 100% Avalanche Tested


**TO-220**

**TO-220F**

**Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AGM10N80C	AGM10N80C	TO-220C	----	----	1000
AGM10N80F	AGM10N80F	TO-220F	-----	----	1000

<b>Absolute Maximum Ratings</b> $T_C = 25^\circ\text{C}$ , unless otherwise noted			
Parameter	Symbol	Value TO-220	Unit
Drain-Source Voltage ( $V_{GS} = 0V$ )	$V_{DSS}$	800	V
Continuous Drain Current	$I_D$	10	A
Pulsed Drain Current (note1)	$I_{DM}$	36	A
Gate-Source Voltage	$V_{GSS}$	$\pm 30$	V
Single Pulse Avalanche Energy (note2)	$E_{AS}$	405	mJ
Avalanche Current (note1)	$I_{AS}$	10	A
Repetitive Avalanche Energy (note1)	$E_{AR}$	243	mJ
Power Dissipation ( $T_C = 25^\circ\text{C}$ )	$P_D$	25	W
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55~+150	$^\circ\text{C}$

<b>Thermal Resistance</b>			
Parameter	Symbol	Value	Unit
		TO-220	
Thermal Resistance, Junction-to-Case	$R_{thJC}$	5	K/W
Thermal Resistance, Junction-to-Ambient	$R_{thJA}$	62.5	

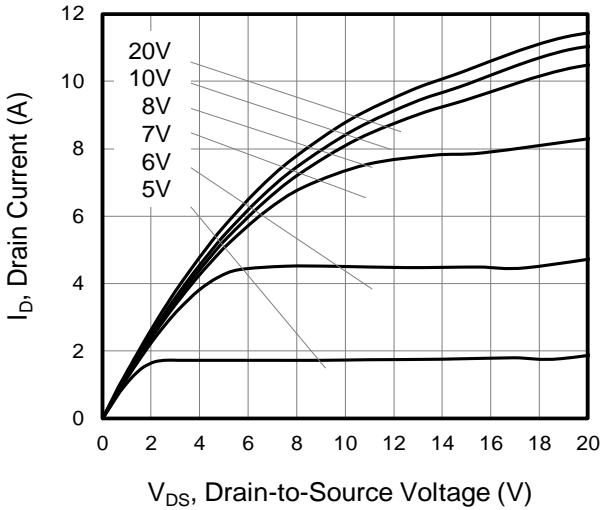
<b>Specifications</b> $T_J = 25^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu\text{A}$	800	--	--	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 800V, V_{GS} = 0V, T_J = 25^\circ\text{C}$	--	--	1	$\mu\text{A}$
		$V_{DS} = 640V, V_{GS} = 0V, T_J = 125^\circ\text{C}$	--	--	100	
Gate-Source Leakage	$I_{GSS}$	$V_{GS} = \pm 30V$	--	--	$\pm 100$	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	3.0	--	4.0	V
Drain-Source On-Resistance (Note3)	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 4.5A$	--	1	1.2	$\Omega$
<b>Dynamic</b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0V,$ $V_{DS} = 25V,$ $f = 1.0\text{MHz}$	--	1519	--	$\mu\text{F}$
Output Capacitance	$C_{oss}$		--	162	--	
Reverse Transfer Capacitance	$C_{rss}$		--	34	--	
Total Gate Charge	$Q_g$	$V_{DD} = 640V, I_D = 9A,$ $V_{GS} = 10V$	--	57	--	nC
Gate-Source Charge	$Q_{gs}$		--	24	--	
Gate-Drain Charge	$Q_{gd}$		--	7.5	--	
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 400V, I_D = 9A,$ $R_G = 25\Omega$	--	45	--	ns
Turn-on Rise Time	$t_r$		--	17	--	
Turn-off Delay Time	$t_{d(off)}$		--	355	--	
Turn-off Fall Time	$t_f$		--	475	--	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Body Diode Current	$I_S$	$T_C = 25^\circ\text{C}$	--	--	10	A
Pulsed Diode Forward Current	$I_{SM}$		--	--	36	
Body Diode Voltage	$V_{SD}$	$T_J = 25^\circ\text{C}, I_{SD} = 4.5A, V_{GS} = 0V$	--	--	1.4	V
Reverse Recovery Time	$t_{rr}$	$V_{GS} = 0V, I_S = 9A,$ $di_F/dt = 100A/\mu\text{s}$	--	562	--	ns
Reverse Recovery Charge	$Q_{rr}$		--	4.399	--	$\mu\text{C}$

**Notes**

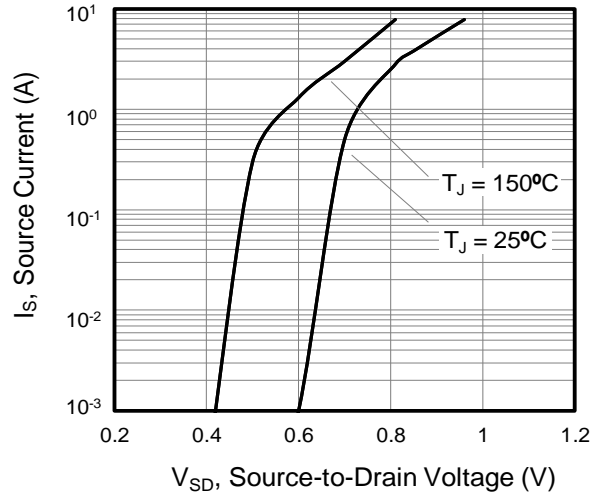
1. Repetitive Rating: Pulse width limited by maximum junction temperature
2.  $L=10\text{mH}, V_{DD} = 50V, R_G = 25\Omega$ , Starting  $T_J = 25^\circ\text{C}$
3. Pulse Test: Pulse width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 1\%$

**Typical Characteristics**  $T_J = 25^\circ\text{C}$ , unless otherwise noted

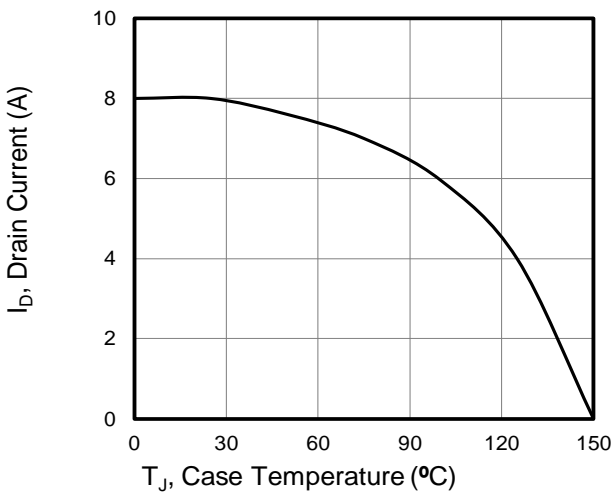
**Figure 1. Output Characteristics ( $T_J = 25^\circ\text{C}$ )**



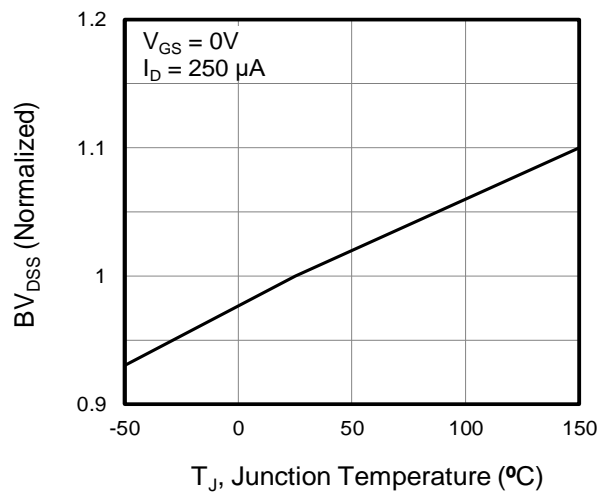
**Figure 2. Body Diode Forward Voltage**



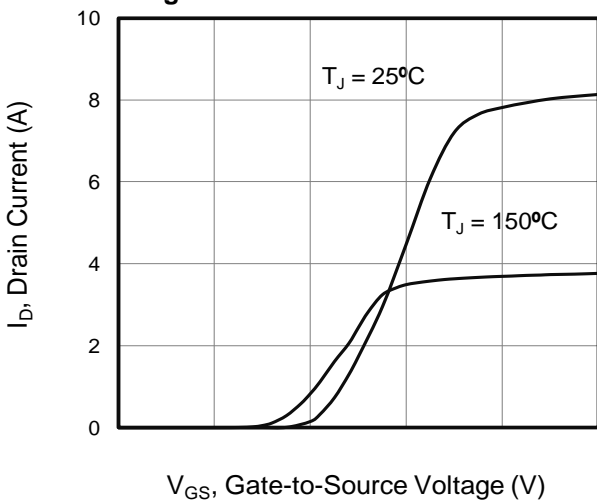
**Figure 3. Drain Current vs. Temperature**



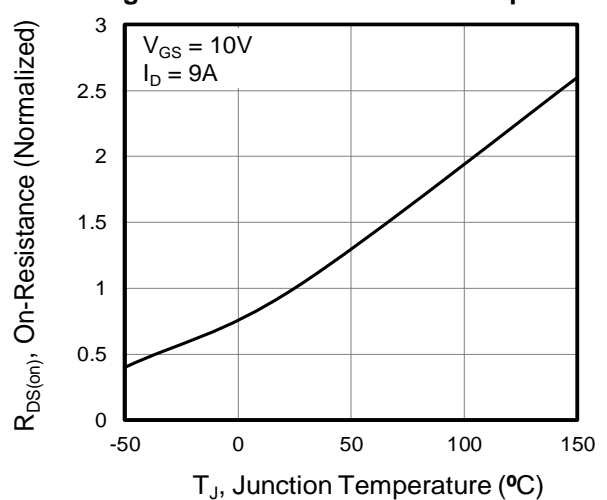
**Figure 4.  $BV_{DSS}$  Variation vs. Temperature**



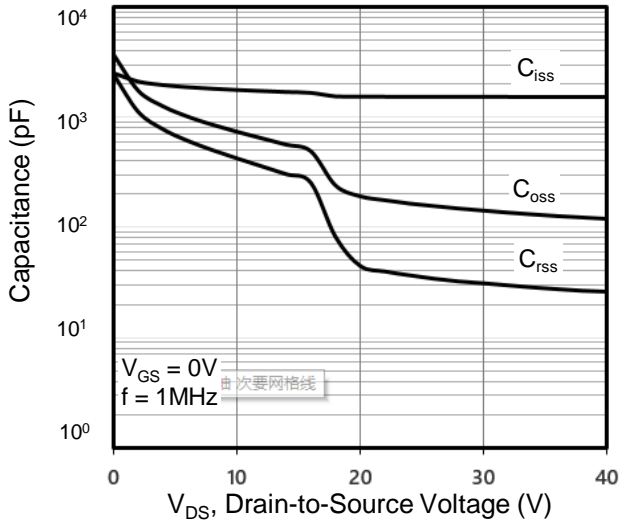
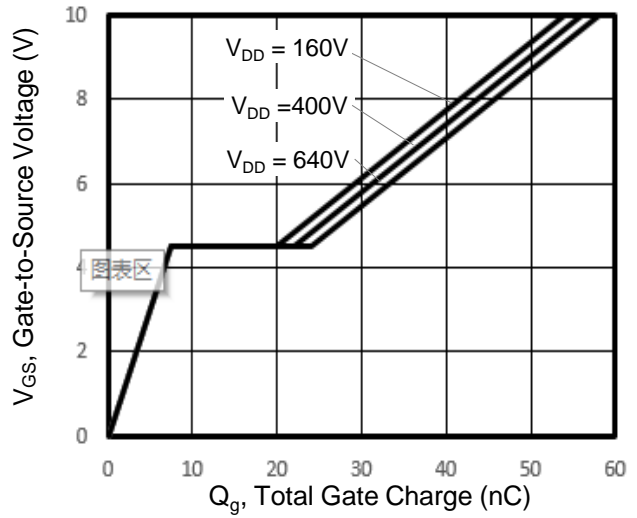
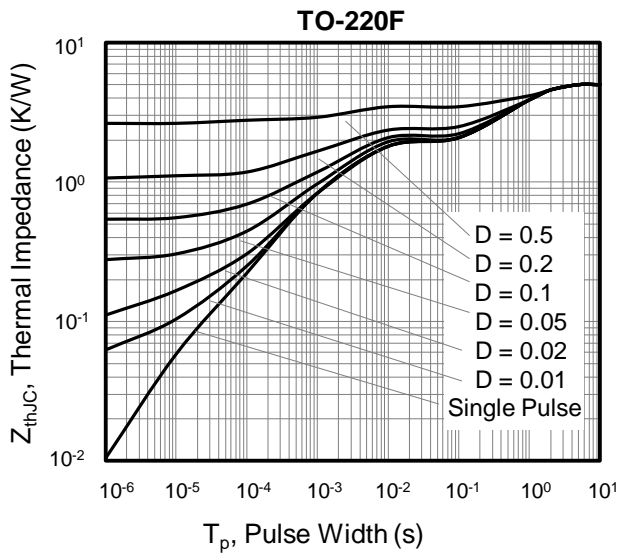
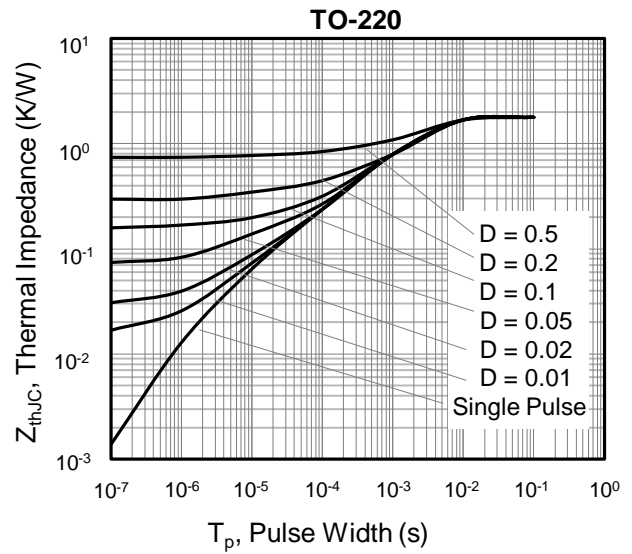
**Figure 5. Transfer Characteristics**

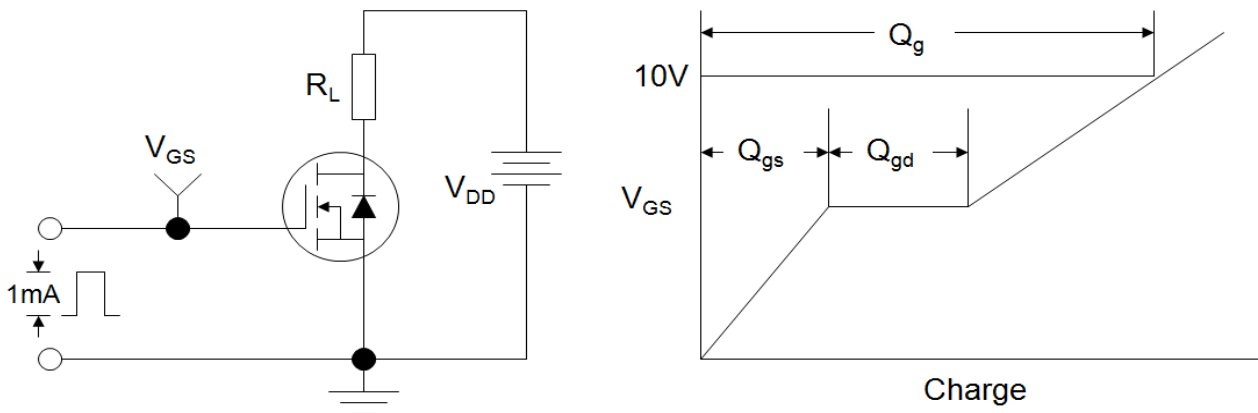
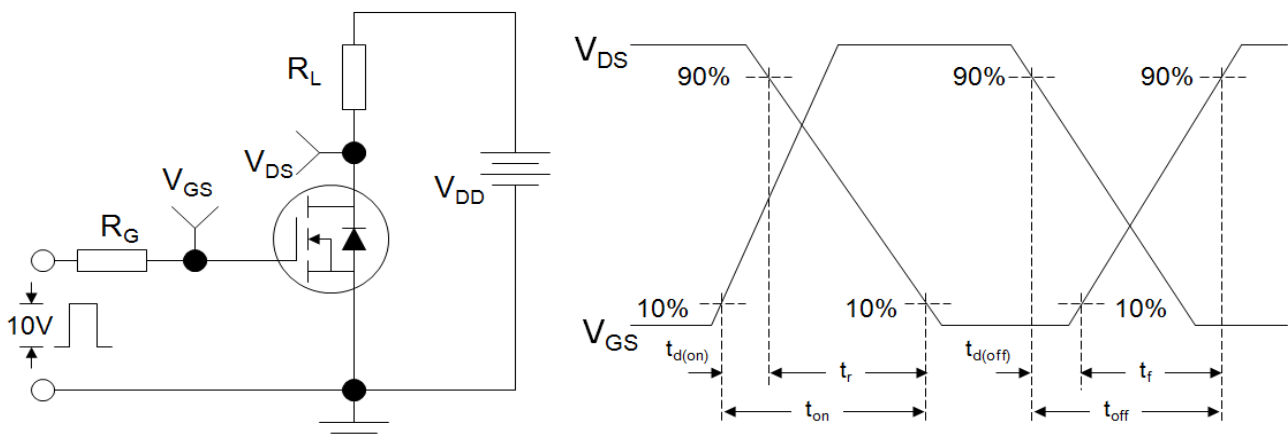
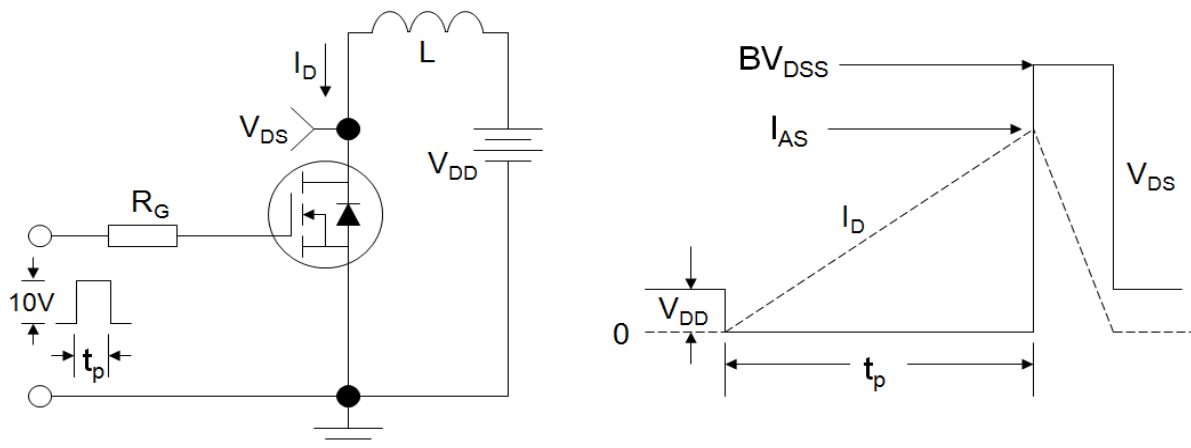


**Figure 6. On-Resistance vs. Temperature**

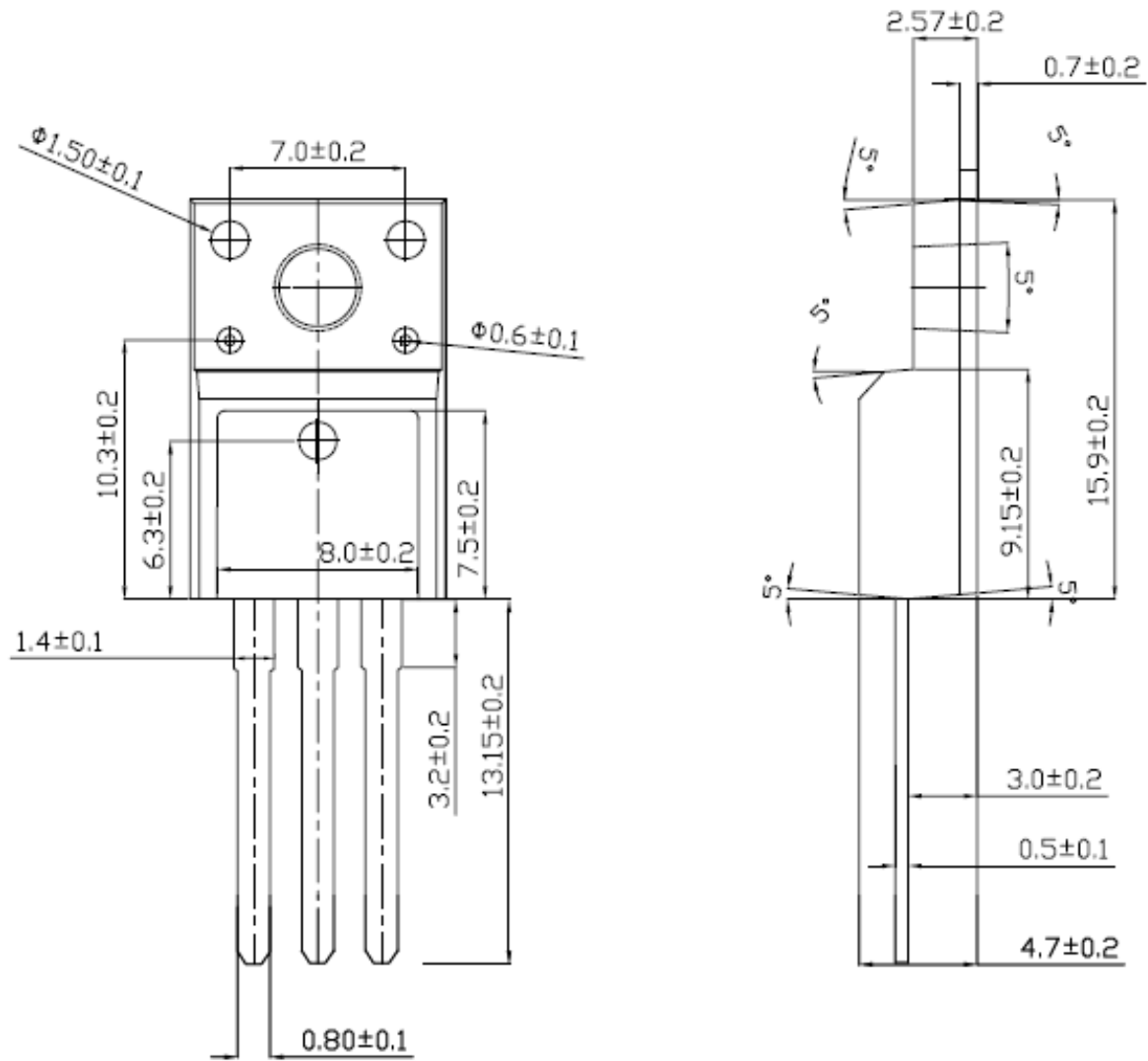


**Typical Characteristics**  $T_J = 25^\circ\text{C}$ , unless otherwise noted

**Figure 7. Capacitance**

**Figure 8. Gate Charge**

**Figure 9. Transient Thermal Impedance**

**Figure 10. Transient Thermal Impedance**


**Figure A: Gate Charge Test Circuit and Waveform**

**Figure B: Resistive Switching Test Circuit and Waveform**

**Figure C: Unclamped Inductive Switching Test Circuit and Waveform**


TO-220F




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